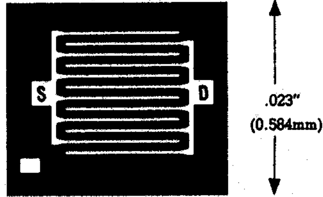
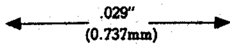
Solitron Devices, Inc.

# P-CHANNEL JUNCTION FET

## CHIP NUMBER

# FP7.3




Die Size: 29 x 23 (mils)
0.737 x 0.584(mm)

Pad Size: 3 x 3 (mils)
0.076 x 0.076(mm)
GATE-SUBSTRATE

### CONTACT METALLIZATION

Top Contact: > 12,000 Å Aluminum

Backside Contact: 3,000 Å Gold

### ASSEMBLY RECOMMENDATIONS

It is advisable that:

a) the die be eutectically mounted with gold silicon preform 98/2%.

b) 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

## TYPICAL ELECTRICAL CHARACTERISTICS

| PARAMETER | MIN. | TYP | MAX. | UNIT | TEST CONDITIONS |
|---|---|---|---|---|---|
| $B_{VGSS}$ | 25 | 40 | 50 | V | $V_{DS} = 0$, $I_G = 1\mu A$ |
| $I_{DSS}$ | -5.0 | -30 | -120 | mA | $V_{DS} = -15V$, $V_{GS} = 0$ |
| $g_{fs}$ | | 10 | | mmho | $V_{DS} = -15V$, $V_{GS}$, $= 0$ |
| $I_{GSS}$ | | 50 | 500 | pA | $V_{GS} = 20V$, $V_{DS} = 0$ |
| $r_{DS}$ | 40 | 100 | 200 | Ω | $V_{DS} = 100mV$, $V_{GS} = 0$ |
| $V_{GS(off)}$ | 1.0 | 4.0 | 10 | V | $V_{DS} = -15V$, $I_D = 1nA$ |
| $C_{rss}$ | | 4.5 | | pF | $V_{DS} = 0$, $V_{GS} = 10V$, $f = 1MHz$ |
| $C_{iss}$ | | 20 | 25 | pF | $V_{DS} = -15V$, $V_{GS} = 0$, $f = 1MHz$ |

TYPICAL DEVICE TYPES: 2N5018, 2N5019, 2N5114 - 2N5116, 2N5319

# CHIP TYPE FP7.3